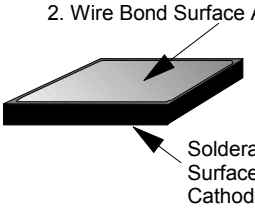
SB063P200-W-Ag/Al
Schottky Barrier Diode Wafer
63 Mils, 200 Volt, 3 Amp

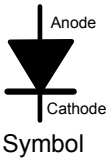
Data Sheet

Features

Oxide Passivated Junction
Low Forward Voltage
150 ° C Junction Operating
Low Reverse Leakage
Supplied as Wafers
Platinum Barrier

1. Solderable Surface Ti/Ni/Ag - Suffix "Ag"
2. Wire Bond Surface Aluminium - Suffix "Al"





Symbol

Electrical Characteristics @ 25°C	Symbol	Unit	SB063P200-W-Ag/Al (See ordering code below)
Maximum Repetitive Reverse Voltage (2)	V_{RRM}	Volt	200
Maximum Forward Voltage (1)(2)	V_F	Volt	0.83
Typical Average Forward Rectified Current (2)	$I_{F(AV)}$	Amp	3
Reverse Leakage Current (2)	I_R	µA	10
Reverse Leakage Current @ 125° C (2)	I_R	mA	5
Junction Operating Temperature Range (2)	T_J	°C	-65 to +150
Storage Temperature Range (2)	T_{SG}	°C	-65 to +150

(1) Pulse Width tp = < 300µS, Duty Cycle <2%
(2) The characteristics above assume the die are assembled in industry standard packages using appropriate attach methods.

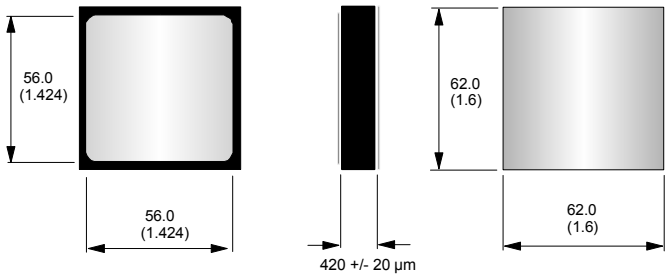
Ordering Code
SB040P150-W-Ag
Schottky Barrier 40 Mils Pt Barrier 150 Volt Wafer Ti/Ni/Ag

Mechanical Dimensions

Wafer

- Wafer Diameter - 100 mm (4")
- Wafer Thickness 420 +/- 20
- Top (Anode) - Ti/Ni/Ag (Suffix "Ag")
  or Aluminium (Suffix "Al")
- Bottom (cathode) Ti/Ni/Ag

Die



Third Angle Protection

Dimensions in mils (mm)

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